Abstracts

A low-current and low-distortion wideband amplifier using 0.2-/spl mu/m gate MODFET fabricated by using phase-shift lithography

H. Ishida, K. Miyatsuji, T. Tanaka, H. Takenaka, H. Furukawa, M. Nishitsuji, A. Tamura and D. Ueda. "A low-current and low-distortion wideband amplifier using 0.2-/spl mu/m gate MODFET fabricated by using phase-shift lithography." 2000 Transactions on Microwave Theory and Techniques 48.5 (May 2000 [T-MTT]): 771-776.

We have developed a wide-band amplifier that can keep a gain over 10 dB at an operation current of 10 mA from 100 MHz to 3 GHz. The fabricated integrated circuit (IC) achieved a high-output third-order intercept point of 30 dBm and low noise figure of 1.6 dB at 800 MHz, respectively. The present IC employs a MODFET with 0.2-/spl mu/m gate fabricated by using a phase-shift lithography technique.

❑ Return to main document.